MITSUBISHI SEMICONDUCTOR < Application Specific Intelligent Power Module>

PS12014-A

FLAT-BASE TYPE INSULATED TYPE



INTEGRATED FUNCTIONS AND FEATURES

- 3-Phase IGBT inverter bridge configured by the latest 3rd. generation IGBT and diode technologies.
- Circuit for dynamic braking of motor regenerative energy.
- Inverter output current capability lo (Note 1):

Type Name	100% load	150% over load
PS12014-A	3.4A (rms)	5.1A (rms), 1min

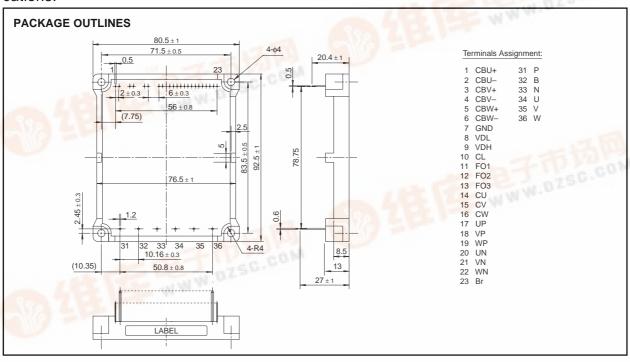
(Note 1): The inverter output current is assumed to be sinusoidal and the peak current value of each of the above loading cases is defined as: $lop = lo \times \sqrt{2}$

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS:

- For P-Side IGBTs: Drive circuit, High-speed photo-couplers, Short circuit protection (SC), Bootstrap circuit supply scheme (Single drive power supply) and Under-voltage protection (UV).
- For N-Side IGBTs: Drive circuit, Short-circuit protection (SC), Control supply Under voltage and Over voltage protection (OV/UV),
 System Over temperature protection (OT), Fault output signaling circuit (Fo), and Current-Limit warning signal output (CL).
- For Brake circuit IGBT : Drive circuit.
- Warning and Fault signaling:
 - Fo1: Short circuit protection for lower-leg IGBTs and Input interlocking against spurious arm shoot-through.
 - Fo2: N-side control supply abnormality locking (OV/UV)
 - Fo3: System over-temperature protection (OT).
 - CL: Warning for inverter current overload condition
- For system feedback control: Analogue signal feedback reproducing actual inverter output phase current (3\$).
- Input Interface: 5V CMOS/TTL compatible, Schmitt trigger input, and Arm-Shoot-Through interlock protection.

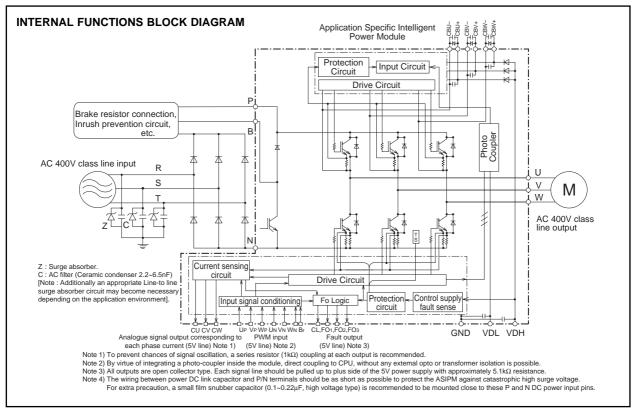
APPLICATION

Acoustic noise-less 0.75kW/AC400V Class 3 Phase inverter and other motor control applications.





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(Fig. 2)

MAXIMUM RATINGS (Tj = 25° C)

INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	900	V
VCC(surge)	Supply voltage (surge)	Applied between P-N, Surge-value	1000	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	1200	V
VP(S) or VN(S)	Each output IGBT collector-emitter surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	1200	V
±lc(±lcp)	Each output IGBT collector current	Tc = 25°C	±10 (±20)	Α
Ic(Icp)	Brake IGBT collector current		5 (10)	Α
IF(IFP)	Brake diode anode current	Note : "()" means lc peak value	5 (10)	Α

CONTROL PART

Symbol	Item	Condition	Ratings	Unit
VDH, VDB	Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	20	V
VDL	Supply voltage	Applied between VDL-GND	7	V
VCIN	Input signal voltage	Applied between UP · VP · WP · UN · VN · WN · Br-GND	−0.5 ~ VDL+0.5	V
VFO	Fault output supply voltage	Applied between Fo1 · Fo2 · Fo3-GND	-0.5 ~ 7	V
IFO	Fault output current	Sink current of F01 · F02 · F03	15	mA
VCL	Current-limit warning output voltage	Applied between CL-GND	-0.5 ~ 7	V
ICL	CL output current	Sink current of CL	15	mA
Ico	Analogue-current-signal output current	Sink current of CU · CV · CW	±1	mA



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TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	−20 ~ +125	°C
Tstg	Storage temperature	_	−40 ~ +125	°C
Tc	Module case operating temperature	(Fig. 3)	−20 ~ +100	°C
Viso	Isolation voltage	60 Hz sinusoidal AC for 1 minute, between all terminals and base plate.	2500	Vrms
_	Mounting torque	Mounting screw: M3.5	0.78 ~ 1.27	N⋅m

Note 2): The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure instantaneous junction temperature as high as 150°C. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is to be provided before use.

CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



(Fig. 3)

THERMAL RESISTANCE

Symbol	Item	Condition		Unit		
Symbol	item		Min.	Тур.	Max.	Offic
Rth(jc)Q	- -	Inverter IGBT (1/6)	_	_	2.0	°C/W
Rth(jc)F		Inverter FWDi (1/6)	_	_	5.5	°C/W
Rth(jc)QB		Brake IGBT	_	_	3.0	°C/W
Rth(jc)FB		Brake FWDi	_	_	7.3	°C/W
Rth(c-f)	Contact Thermal Resistance	Case to fin, thermal grease applied (1 Module)	_	_	0.040	°C/W

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V, VDL = 5V unless otherwise noted)

Symbol	lane	Condition		Ratings			
Symbol	Item			Тур.	Max.	Unit	
VCE(sat)	Collector-emitter saturation $VDL = 5V$, $VDH = VDB = 15V$ Input = ON, $Tj = 25^{\circ}C$, Ic = 10A		_	_	3.6	V	
VEC	FWDi forward voltage	voltage Tj = 25°C, Ic = -10A, Input = OFF		_	3.5	V	
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	VDL = 5V, VDH = 15V Input = ON, Tj = 25°C, Ic = 5A	_	_	3.6	V	
VFBr	Brake diode forward voltage	Tj = 25°C, IF = 5A, Input = OFF	_	_	3.5	V	
ton		1/2 Bridge inductive, Input = ON	0.3	1.2	2.0	μs	
tc(on)	Switching times	Vcc = 600V, Ic = 10A, Tj = 125°C	_	0.5	1.4	μs	
toff	Switching times	VDL = 5V, VDH = 15V, VDB = 15V	_	2.2	4.0	μs	
tc(off)		Note : ton, toff include delay time of the internal control		0.9	1.6	μs	
trr	FWD reverse recovery time	circuit.	_	0.2	_	μs	
	Short circuit endurance	Vcc ≤ 800V, Input = ON (One-Shot)	No destruction				
	(Output, Arm, and Load, Short	Tj = 125°C start	Fo output by protection o		action one	neration	
	Circuit Modes)	13.5V ≤ VDH = VDB = ≤ 16.5V	o to output by protection oper				
		Vcc ≤ 800V, Tj ≤ 125°C,	No destructionNo protecting operationNo Fo output				
	Switching SOA	Ic < IoL(CL) operation level, Input = ON,					
		13.5V ≤ VDH = VDB = ≤ 16.5V					
ldн	VDH Circuit Current	VDL = 5V, VDH = 15V, VCIN = 5V	_	_	150	mA	
IDL	VDL Circuit Current	VDL = 5V, VDH = 15V, VCIN = 5V	_	_	50	mA	
Vth(on)	Input on threshold voltage		8.0	1.4	2.0	V	
Vth(off)	Input off threshold voltage		2.5	3.0	4.0	V	
Ri	Input pull-up resistor Integrated between input terminal-VDH		_	150	_	kΩ	



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ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V, VDL = 5V unless otherwise noted)

Curahal	Item		Condition		-	Ratings		Unit		
Symbol					Min.	Тур.	Max.			
fPWM	PWM input fred	quency		Tc ≤ 100°C, Tj ≤ 125°C		2	_	15	kHz	
txx	Allowable input on-pulse width		VDH = 15V, VDL =	= 5V, Tc = -20°C ~ +100°C	Note 3)	2	_	500	μs	
tdead	Allowable input signal dead time for blocking arm shoot-through		Relates to corres	sponding inputs (Except brake 00°C	e part)	4.0	_	_	μs	
tint	Input inter-lock	sensin	g	Relates to corres	ponding inputs (Except brake	e part)	_	65	100	ns
Vco				Ic = 0A	VDH = 15V		1.87	2.27	2.57	V
VC+(200%)	Analogue signa	al linea	rity with	Ic = IOP(200%)	VDL = 5V		0.77	1.17	1.47	V
VC-(200%)	output current			Ic = -IOP(200%)	Tc = -20 ~ 100°C	(Fig.4)	2.97	3.37	3.67	V
ΔVco	Offset change are	a vs ten	nperature	VDH = 15V, VDL =	5V, Tc = −20 ~ 100°C		_	15	_	mV
VC+				Ic > IOP(200%), VE	DH = 15V,		_	_	0.7	V
Vc-	Analogue signal output voltage limit		VDL = 5V		(Fig. 4)	4.0	_	_	V	
ΔVc(200%)	Analogue signal overall linear variation		VCO-VC±(200%)			_	1.1	_	V	
rCH	Analogue signal data hold accuracy		hold	Correspond to m	ax. 500μs data hold period o	nly, (Fig. 5)	-5	_	5	%
td(read)	Analogue signal reading time		After input signal	trigger point	(Fig. 8)	_	3	_	μs	
ICL(H)	Signal output	cur-	Idle	Open collector onput		_	_	1	μΑ	
ICL(L)	rent of CL oper		Active			_	1	_	mA	
±loL	CL warning ope	eration	level	VDL = 5V, VDH =	15V, Tc = −20 ~ 100°C	(Note 4)	9.14	11.05	13.90	А
SC	Short circuit cu	rrent tr	ip level	Tj = 25°C	(Fig. 7)	, (Note 5)	15.30	26.80	38.90	Α
ОТ	Over tenperature	Trip	level	VDL = 5V, VDH = 15V		100	110	120	°C	
OTr	protection	Rese	et level			_	90	_	°C	
UVdb		Trip	level				10.0	11.0	12.0	V
UVDBr		Rese	et level				10.5	11.5	12.5	V
UVDH	Supply circuit	Trip	level	To 20°C .1	0000		11.05	12.00	12.75	V
UVDHr	under and over voltage	Rese	et level	Tc = -20°C ~ +10 Tj ≤ 125°C	00°C		11.55	12.50	13.25	V
OVDH	protection	Trip	level				18.00	19.20	20.15	V
OVDHr	Reset level Filter time				16.50	17.50	18.65	V		
tdv					_	10		μs		
IFO(H)	Fault output cu	ırront	Idle	On an application of			_	_	1	μA
IFO(L)	i adii odipul Cl	aireiit	Active	Open collector or	uipui ——————————————————————————————————		_	1	_	mA

(Note 3) : (a) Allowable minimum input on-pulse width : This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width : This item applies to both P-side and N-side circuits excluding the brake circuit.

(Note4) : CL output : The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5) : The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momen-

tarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

RECOMMENDED CONDITIONS

Cumbal	la	Condition		Ratings			
Symbol	Item	Condition	Min.	Тур.	Max.	Unit	
Vcc	Supply voltage	Applied between P-N	_	600	800	V	
VDH, VDB	Control supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	13.5	15.0	16.5	V	
VDL	Control supply voltage	Applied between VDL-GND	4.8	5.0	5.2	V	
$\Delta V_{DH}, \Delta V_{DB}, \\ \Delta V_{DL}$ Supply voltage ripple			-1	_	+1	V/µs	
VCIN(on)	Input ON voltage		_	_	0.3	V	
VCIN(off)	Input OFF voltage		4.8	_	_	V	
fPWM	PWM Input frequency	Using application circuit	2	10	15	kHz	
tdead	Arm shoot-through blocking time	Using application circuit	4.0	_	_	μs	



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Fig. 4 OUTPUT CURRENT ANALOGUE SIGNALING LINEARITY

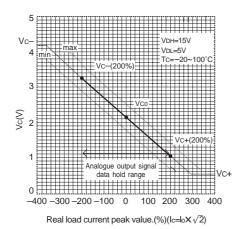
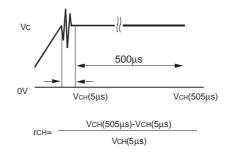
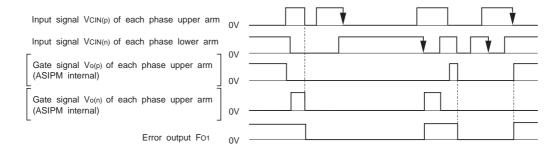


Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 us delayed point.

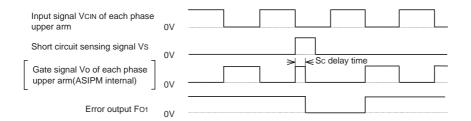
Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note: Input interlock protection circuit; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION



Note: Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").



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Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART.

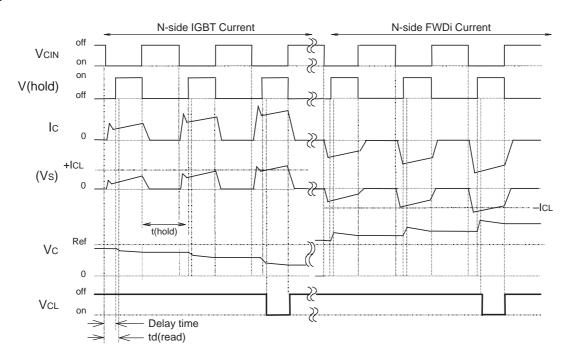


Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to VDL voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph

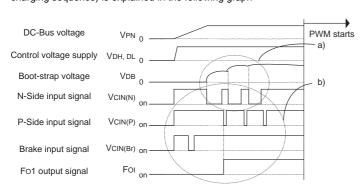
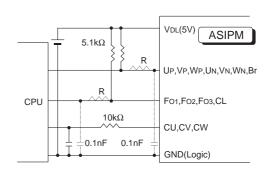


Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT



a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. 20μs number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br \rightarrow Un/Vn/Wn \rightarrow Up/Vp/Wp in that order.

